Amendments to the Claims:

Please amend claims 37, 82, 86, 90 and 95 as follows:

Listing of Claims:

1-36. (Cancelled)

~~37.~~ (Currently Amended) A method of forming a semiconductor device, comprising:

depositing a first conductive layer having a surface and having an ability to associate with oxygen;

incorporating an oxygen-free material directly into said surface to passivate the surface of said first conductive layer to reduce the ability of the first conductive layer to associate with oxygen, the oxygen-free material being ~~selected from a group consisting of phosphine and~~ methylsilane;

depositing a second conductive layer on said surface after incorporating the oxygen-free material into the surface;

exposing said second conductive layer to a thermal process;

and wherein said step of depositing a first conductive layer comprises depositing a capacitor plate;

and wherein said method further comprises depositing an insulator over said second conductive layer; and

said step of exposing said second conductive layer to a thermal process comprises flowing said insulator.

~~38.~~ (Previously Presented) The method in claim ~~37~~, wherein:

said step of depositing a first conductive layer comprises depositing a plug; and

said step of exposing said second conductive layer to a thermal process comprises

flowing said second conductive layer.

39. (Previously Presented) The method in claim 37, wherein said step of exposing said second conductive layer to a thermal process comprises exposing said second conductive layer to an alloy process.

40-75. (Cancelled)

76. (Previously Presented) A method of forming a semiconductor device, comprising:

depositing a tungsten nitride layer having a surface;

incorporating an oxygen-free material directly into the surface of the tungsten nitride layer to passivate the surface of the tungsten nitride layer to reduce an ability of the tungsten nitride layer to associate with oxygen;

depositing a conductive layer on the surface of the tungsten nitride layer after incorporating the oxygen-free material into the surface of the tungsten nitride layer; and

exposing the conductive layer to a thermal process.

77. (Previously Presented) The method in claim 76 wherein depositing a tungsten nitride layer forms a capacitor plate and wherein the process further comprises depositing an insulator over the conductive layer and wherein exposing the conductive layer to a thermal process comprises flowing the insulator.

78. (Previously Presented) The method of claim 77 wherein the conductive layer comprises copper.

79. (Previously Presented) The method in claim 76 further comprising depositing a plug on which the tungsten nitride layer is thereafter deposited, and wherein exposing the conductive layer to a thermal process comprises flowing the conductive layer.

80. (Previously Presented) The method in claim 76, wherein exposing the conductive layer to a thermal process comprises exposing the conductive layer to an alloy process.

81. (Cancelled)

82. (Currently Amended) A method of forming a semiconductor device, comprising

providing a first conductive layer having a surface and having an ability to associate with oxygen;

placing the surface of the first conductive layer in direct contact with an oxygen-free atmosphere under appropriate conditions to passivate the surface and reduce the ability of the first conductive layer to associate with oxygen, the oxygen-free atmosphere including ~~a material selected from a group consisting of phosphine and~~ methylsilane;

providing a second conductive layer on the surface of the first conductive layer;

subjecting the second conductive layer to a thermal process; and wherein depositing a first conductive layer forms a capacitor plate and wherein the process further comprises depositing an insulator over the second conductive layer and wherein exposing the second conductive layer to a thermal process comprises flowing the insulator.

83. (Previously Presented) The method of claim 82 wherein the second conductive layer comprises copper.

84. (Previously Presented) The method in claim 82 further comprising depositing a plug on which the first conductive layer is thereafter deposited, and wherein exposing the second conductive layer to a thermal process comprises flowing the second conductive layer.

85. (Previously Presented) The method in claim 82, wherein exposing the conductive layer to a thermal process comprises exposing the conductive layer to an alloy process.

86. (Currently Amended) A method of forming a semiconductor device, comprising:

depositing a first conductive layer having a surface and having an ability to associate with oxygen;

incorporating ~~a selection consisting of phosphine and~~ methylsilane ~~and combinations thereof~~ directly into the surface to passivate the surface of the first conductive layer to reduce the ability of the first conductive layer to associate with oxygen;

depositing a second conductive layer on the surface after incorporating the oxygen-free material into the surface; and

exposing the second conductive layer to a thermal process.

87. (Previously Presented) The method in claim 86, wherein depositing a first conductive layer comprises depositing a capacitor plate and wherein the method further comprises depositing an insulator over the second conductive layer, and wherein exposing the second conductive layer to a thermal process comprises flowing the insulator.

88. (Previously Presented) The method in claim 86, wherein the step of depositing a first conductive layer comprises depositing a plug and wherein exposing the second conductive layer to a thermal process comprises flowing the second conductive layer.

89. (Previously Presented) The method in claim 36, wherein exposing the second conductive layer to a thermal process comprises exposing the second conductive layer to an alloy process.

~~90~~. (Currently Amended) A method of forming a semiconductor device, comprising:

depositing a tungsten nitride layer having a surface;

incorporating a selection consisting of diborane, ~~phosphine,~~ methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof directly into the surface of the tungsten nitride layer to passivate the surface of the tungsten nitride layer to reduce an ability of the tungsten nitride layer to associate with oxygen;

depositing a conductive layer on the surface of the tungsten nitride layer after incorporating the selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof into the surface of the tungsten nitride layer; and

exposing the conductive layer to a thermal process.

~~91~~. (Previously Presented) The method of claim ~~90~~ wherein depositing a tungsten nitride layer forms a capacitor plate and wherein the process further comprises depositing an insulator over the conductive layer and wherein exposing the conductive layer to a thermal process comprises flowing the insulator.

~~92~~. (Previously Presented) The method of claim ~~90~~ wherein the conductive layer comprises copper.

~~93~~. (Previously Presented) The method in claim ~~90~~ further comprising depositing a plug on which the tungsten nitride layer is thereafter deposited, and wherein exposing the conductive layer to a thermal process comprises flowing the conductive layer.

94. (Previously Presented) The method in claim 90, wherein exposing the conductive layer to a thermal process comprises exposing the conductive layer to an alloy process.

95. (Currently Amended) A method of forming a semiconductor device, comprising

providing a first conductive layer having a surface and having an ability to associate with oxygen;

placing the surface of the first conductive layer in direct contact with ~~a selection consisting of phosphine and~~ methylsilane, ~~and combinations thereof~~ under appropriate conditions to passivate the surface and reduce the ability of the first conductive layer to associate with oxygen;

providing a second conductive layer on the surface of the first conductive layer; and

subjecting the second conductive layer to a thermal process.

96. (Previously Presented) The method in claim 95 wherein depositing a first conductive layer forms a capacitor plate and wherein the process further comprises depositing an insulator over the second conductive layer and wherein exposing the second conductive layer to a thermal process comprises flowing the insulator.

97. (Previously Presented) The method of claim 96 wherein the second conductive layer comprises copper.

98. (Previously Presented) The method in claim 95 further comprising depositing a plug on which the first conductive layer is thereafter deposited, and wherein exposing the second conductive layer to a thermal process comprises flowing the second conductive layer.

99. (Previously Presented) The method in claim 95, wherein exposing the conductive layer to a thermal process comprises exposing the conductive layer to an alloy process.